Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	l _D
100V	1.1mΩ@10V	370A



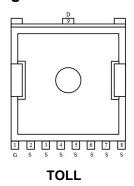
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

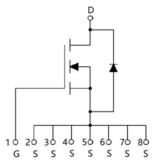
Applications

- PWM Application
- Hard switched and high frequency circuits
- Power Management

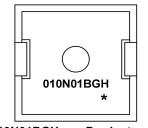
Package



Circuit diagram



Marking



010N01BGH : Product code * : Month code

Order Information

Device	Package	Unit/Tape
SP010N01BGHTO	TOLL	2000

100V N-Channel Power MOSFET

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current1 (Tc=25°ℂ)	I _D	370	Α
Continuous Drain Current1 (Tc=100°C)	I _D	247	Α
Pulsed Drain Current	I _{DM}	1480	Α
Single Pulse Avalanche Energy ¹	Eas	2304	mJ
Power Dissipation (Tc=25°C)	P _D	410	W
Thermal Resistance Junction-to-Case	R _{θJC}	0.3	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	$^{\circ}$
Operating Junction Temperature Range	TJ	-55 to 150	$^{\circ}$

Electrical characteristics (Ta=25°C, unless otherwise noted)

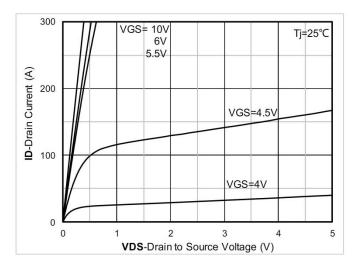
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
Static Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	100	110	-	V
Drain Cut-Off Current	IDSS	VDS=80V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	I _{GSS}	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	VGS=VDS , ID =250uA	2	3	4	V
Drain-Source ON Resistance	R _{DS(ON)}	VGS=10V , ID=125A	-	1.1	1.3	mΩ
Dynamic Characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	-	14658	-	
Output Capacitance	Coss		-	2335	-	pF
Reverse Transfer Capacitance	C _{rss}		-	39	-	
Total Gate Charge	Qg	VDS=50V , VGS=10V , ID=125A	-	208	-	nC
Gate-Source Charge	Q _{gs}		-	56	-	
Gate-Drain Charge	Q _{gd}		-	37	-	
Switching Characteristics			<u> </u>			
Turn-On Delay Time	t _{d(on)}		-	25	-	
Rise Time	tr		-	75	-	nS
Turn-Off Delay Time	t _{d(off)}	VDD=50V, VGS=10V , RG=1.6 Ω ,	-	89	-	
Fall Time	t _f	ID=125A	-	29	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, VGS = 0V	-	-	1.2	V
Maximum Body-Diode Continuous Current	Is		-	-	370	Α
Reverse Recovery Time	Trr	l₅=100A, di/dt=100A/us, TJ=25℃	-	92	-	nS
Reverse Recovery Charge	Qrr	15-100A, UI/UL-100A/US, 13-23 C	-	302	-	nC

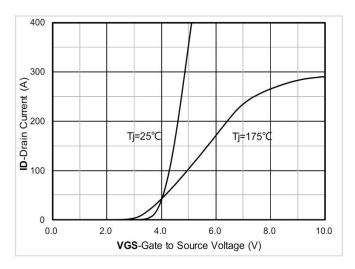
Note:

1. The test condition is VDD=50V,VGS=10V,L=0.5mH,RG=25 Ω

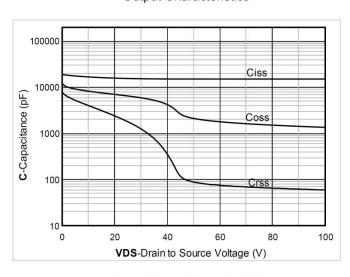
100V N-Channel Power MOSFET

Typical Characteristics

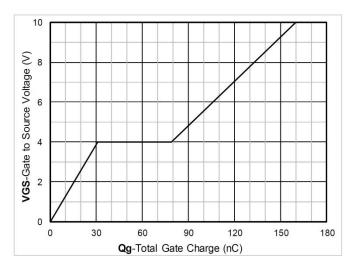




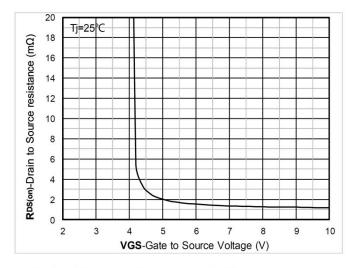
Output Characteristics



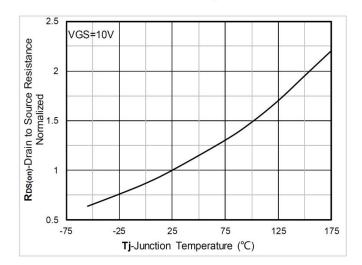
Transfer Characteristics



Capacitance Characteristics



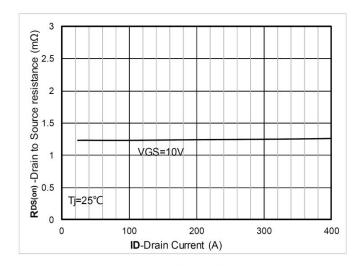
Gate Charge

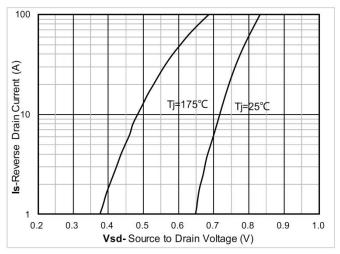


On-Resistance vs Gate to Source Voltage

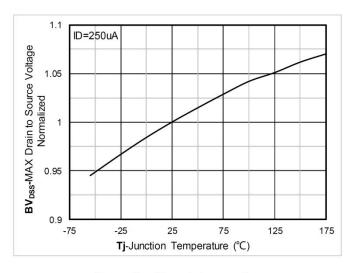
Normalized On-Resistance



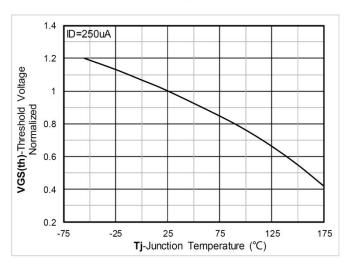




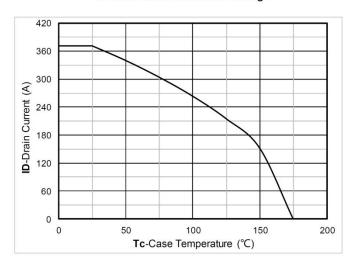
RDS(on) VS Drain Current



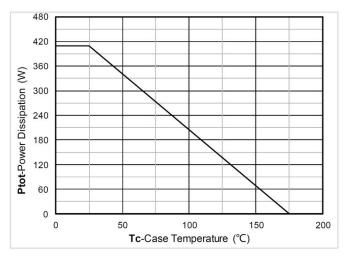
Forward characteristics of reverse diode



Normalized breakdown voltage



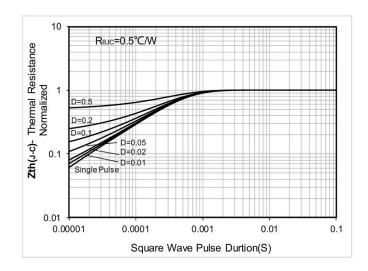
Normalized Threshold voltage

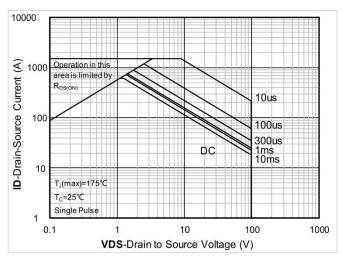


Current dissipation

Power dissipation

100V N-Channel Power MOSFET

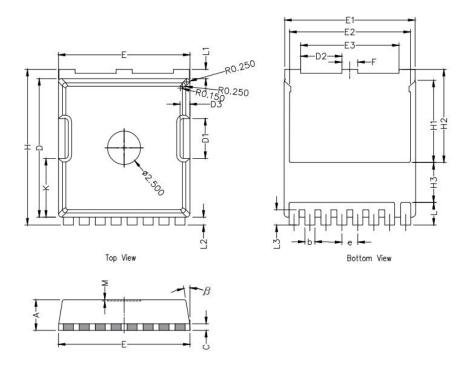




Maximum Transient Thermal Impedance

Safe Operation Area

TOLL Package Information



Symbol	Dimensions In Millimeters			
	Min.	Nom.	Max.	
Α	2.20	2.30	2.40	
b	0.65	0.75	0.85	
С		0.508 REF		
D	10.25	10.40	10.55	
D1	2.85	3.00	3.15	
E	9.75	9.90	10.05	
E1	9.65	9.80	9.95	
E2	8.95	9.10	9.25	
E3	7.25	7.40	7.55	
е		1.20 BSC		
F	1.05	1.20	1.35	
Н	11.55	11.70	11.85	
H1	6.03	6.18	6.33	
H2	6.85	7.00	7.15	
H3		3.00 BSC		
L	1.55	1.70	1.85	
L1	0.55	0.7	0.85	
L2	0.45	0.6	0.75	
М		0.08 REF.		
β	8°	10°	12°	
К	4.25	4.40	4.55	